Silicon NPN Triple Diffused Character Display Horizontal Deflection Output

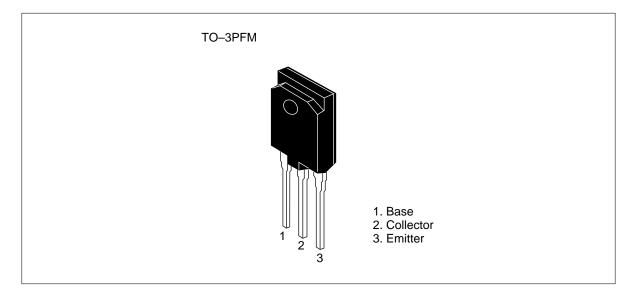
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ADE-208-672 (Z) 1st. Edition Oct. 1, 1998

Features

- High breakdown voltage $V_{CBO} = 1500 \text{ V}$
- High speed switching tf = 0.15 µsec(typ.) at fH=64kHz

Outline



Absolute Maximum Ratings (Ta = 25° C)

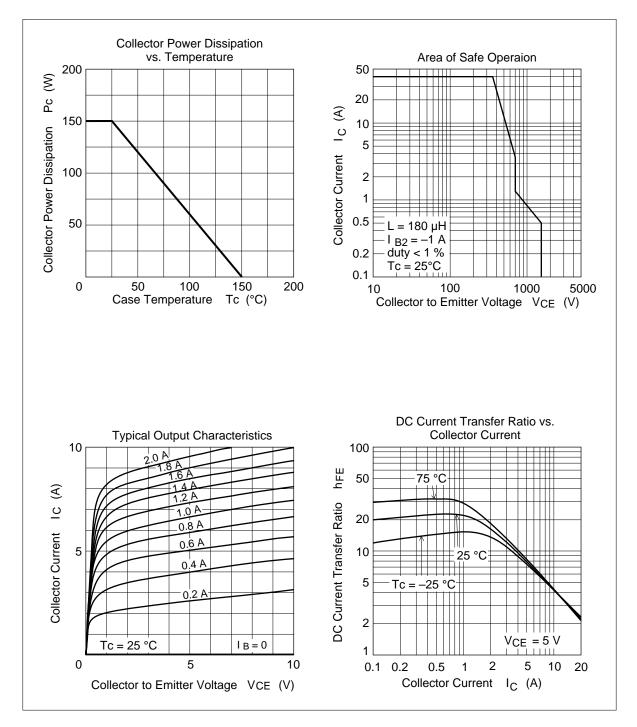
Item	Symbol	Ratings	Unit	Unit	
Collector to base voltage	V _{CBO}	1500	V		
Collector to emitter voltage	V _{CEO}	700	V		
Emitter to base voltage	V _{EBO}	6	V		
Collector current	I _c	20	А		
Collector peak current	İ _{c(peak)}	40	A		
Collector power dissipation	Pc ^{Note1}	150	W		
Junction temperature	Tj	150	°C		
Storage temperature	Tstg	-55 to +150	°C		

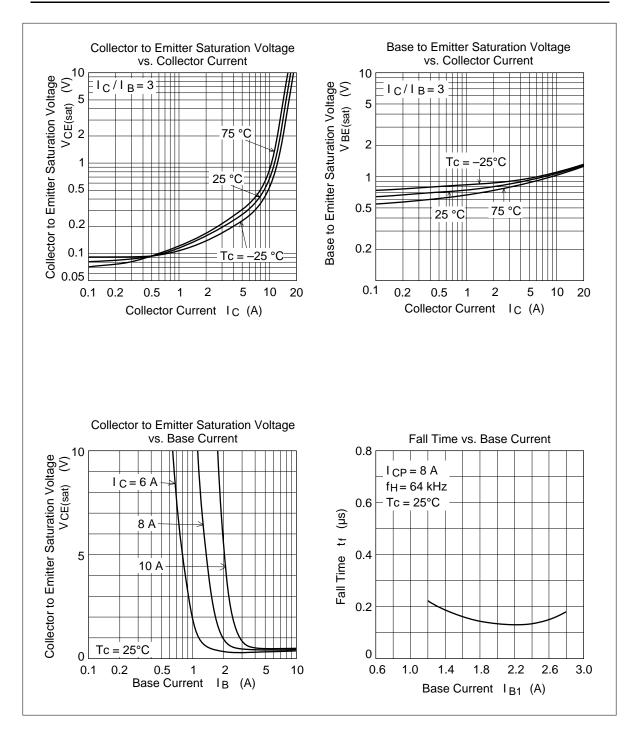
Note: 1. Value at $Tc = 25^{\circ}C$

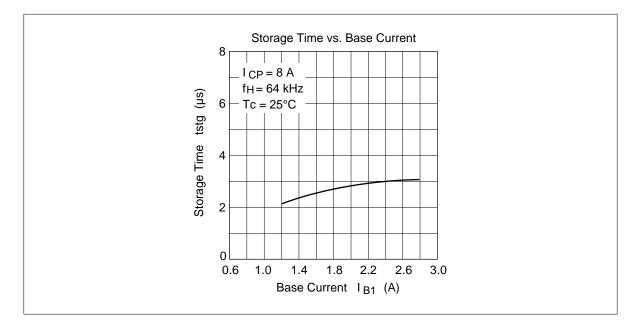
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector to emitter breakdown voltage	V _{(BR)CEO}	700			V	$I_c = 10mA, R_{BE} = \bullet$
Emitter to base breakdown voltage	V _{(BR)EBO}	6			V	$I_{\rm E} = 10 {\rm mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CES}			500	μA	$V_{CE} = 1500V, R_{BE} = 0$
DC current transfer ratio	h _{FE1}	10		40		$V_{ce} = 5 V, I_c = 1A$
DC current transfer ratio	h _{FE2}	3.5		6.5		$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 10 \text{ A}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	5	V	$I_{c} = 12A, I_{B} = 4A$
Base to emitter saturation voltage	V _{BE(sat)}		_	1.5	V	$I_{\rm C} = 12$ A, $I_{\rm B} = 4$ A
Fall time	t _f	_	0.2	0.4	μs	$I_{CP} = 8A, I_{B1} = 3A$ $f_{H} = 31.5 \text{kHz}$
Fall time	t _f	_	0.15		μs	$I_{CP} = 8A, I_{B1} = 2A$ $f_{H} = 64$ kHz

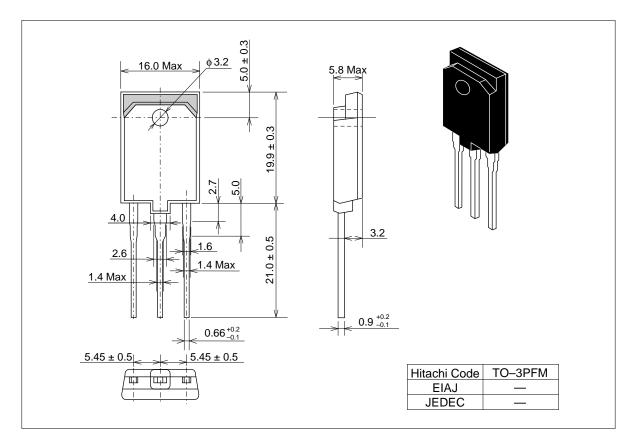
Main Characteristics







Package Dimensions (Unit: mm)



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